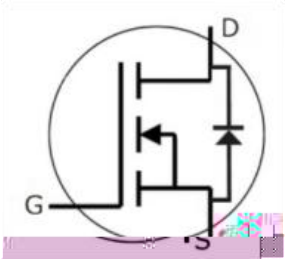
SG2M035120BJ

TriQSiC™ 1200V Silicon Carbide Power MOSFET G2

Features

-
-
-
-
-
-
-



Benefits

-
-
-
-
-

Part number	Die size W x L mm

Applications

-
-
-
-

Table 1 Key performance and package parameters

Type	V_{DS}	I_{DS} ≤	$R_{DS(on),\ typ}$	$T_{J,max}$

1 Maximum ratings

Table 2 Maximum rating

Symbol	Parameter	Value	Unit	Test Conditions	Note

SG2M035120BJ

2.3 Switching characteristics

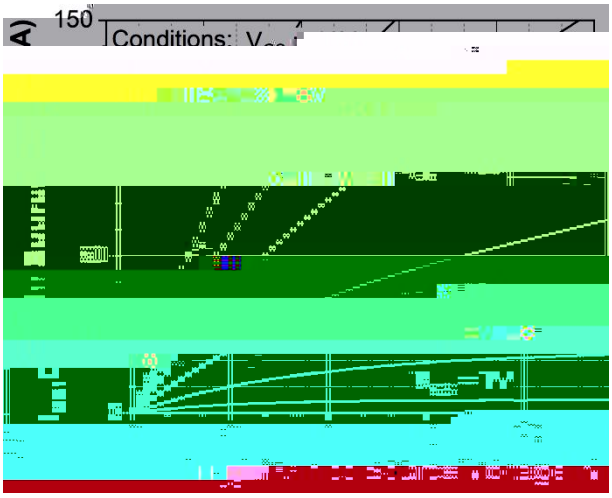
Table 6 Dynamic characteristics

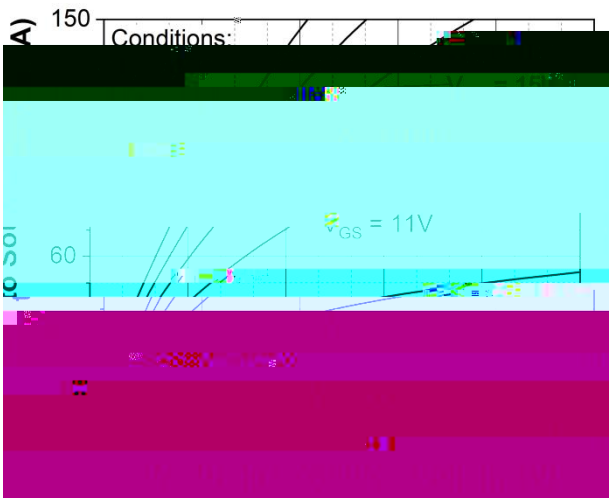
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

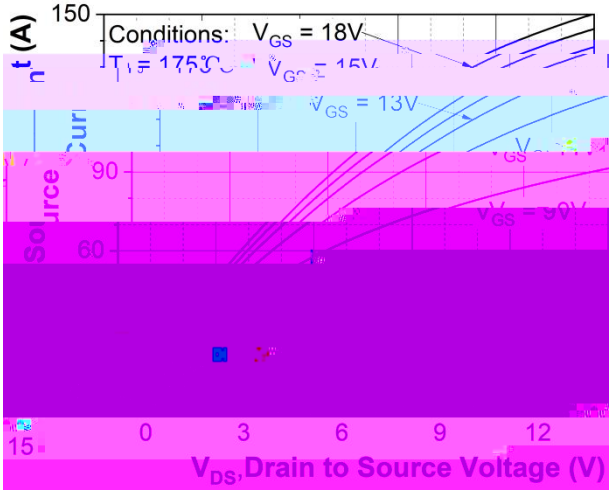
Table 7 Body diode characteristics

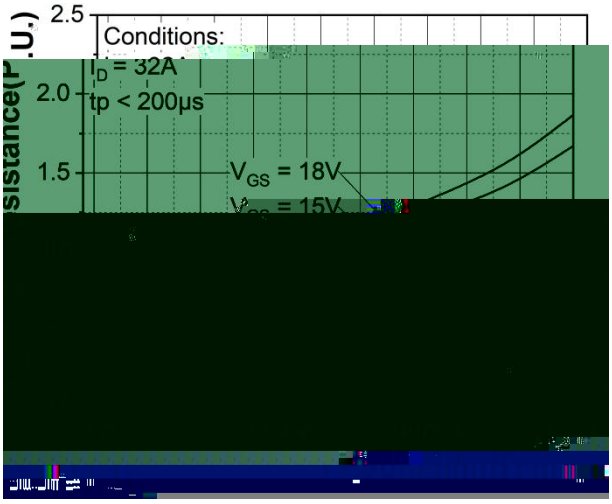
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

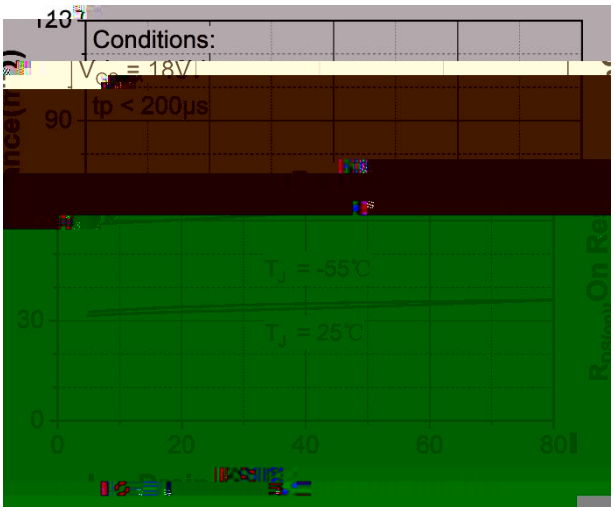
3 Electrical characteristic diagrams

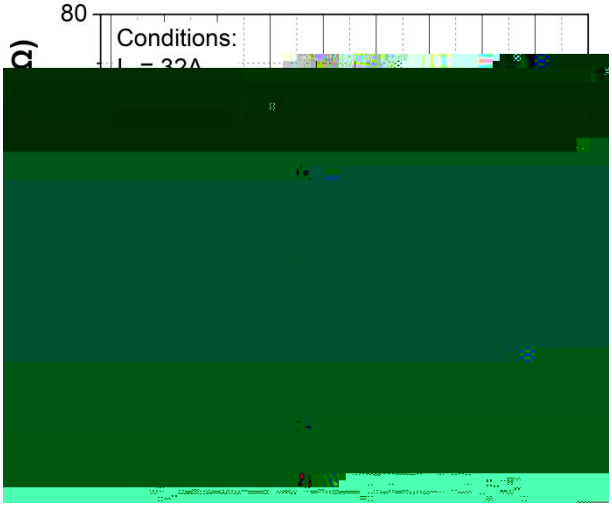




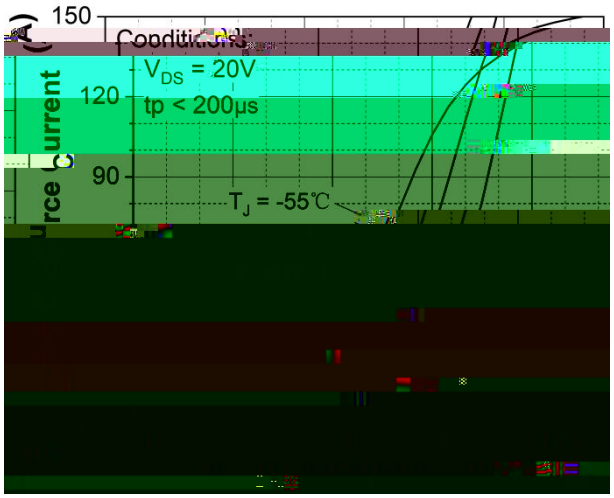


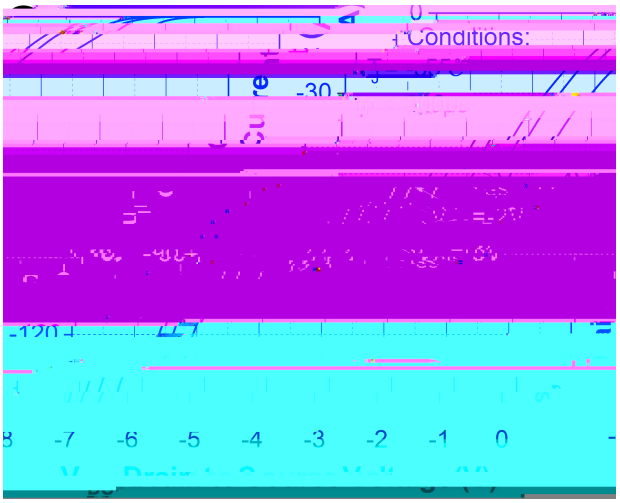


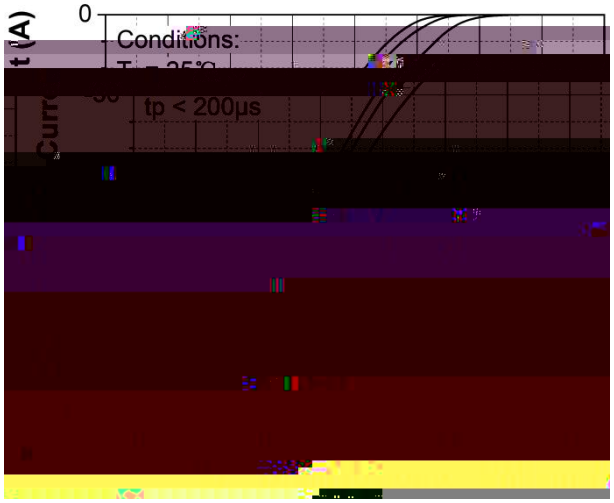


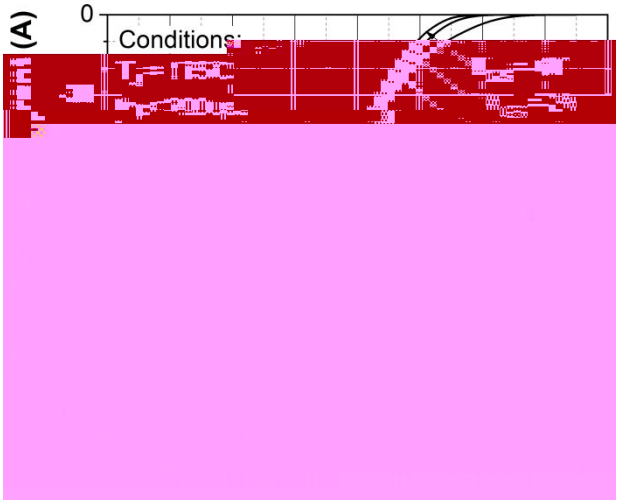


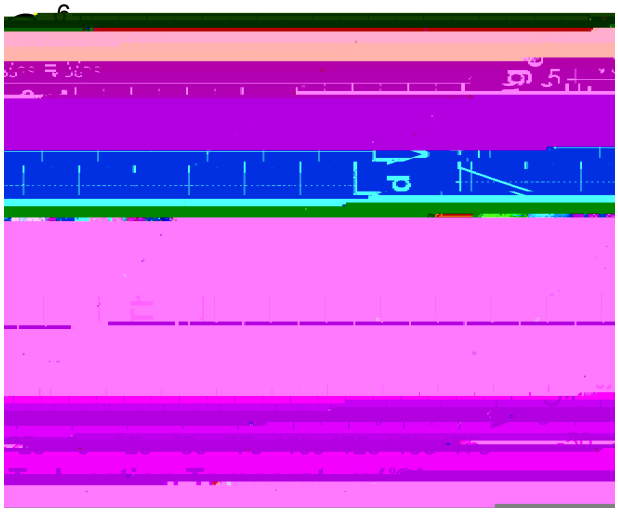
SG2M035120BJ

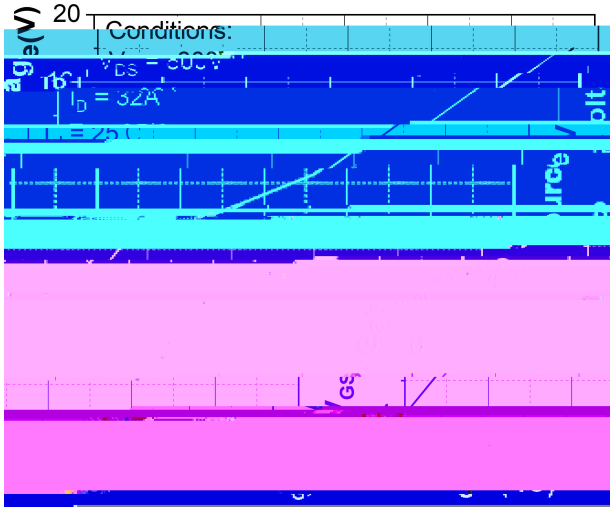




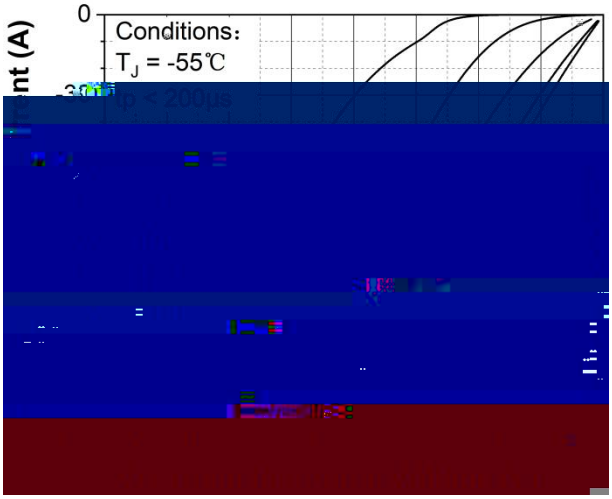


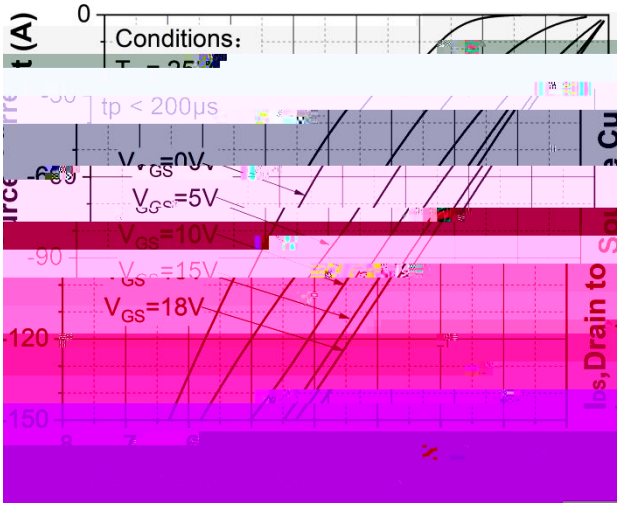


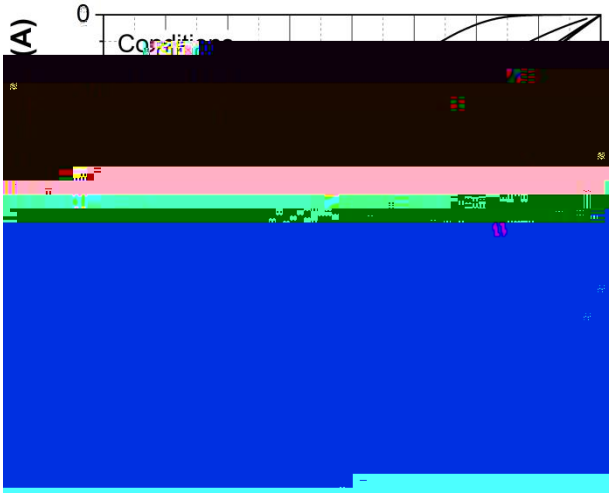


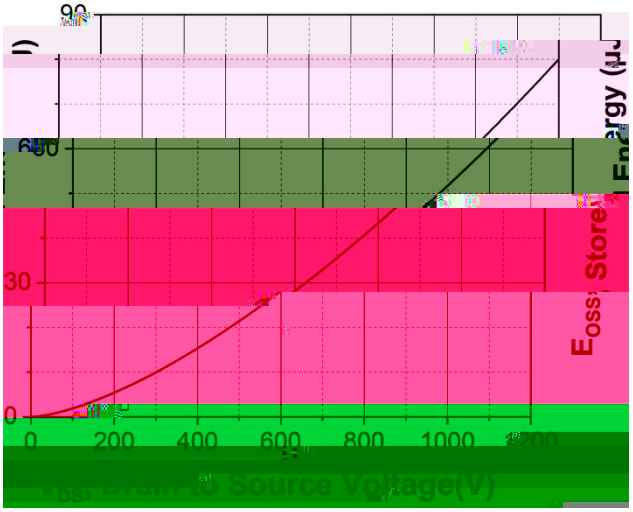


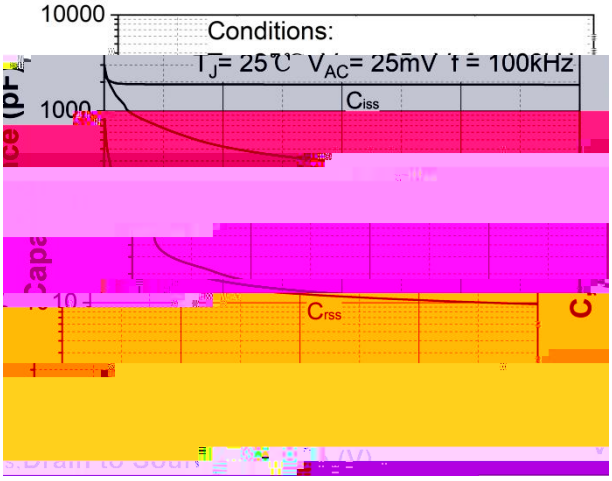
SG2M035120BJ

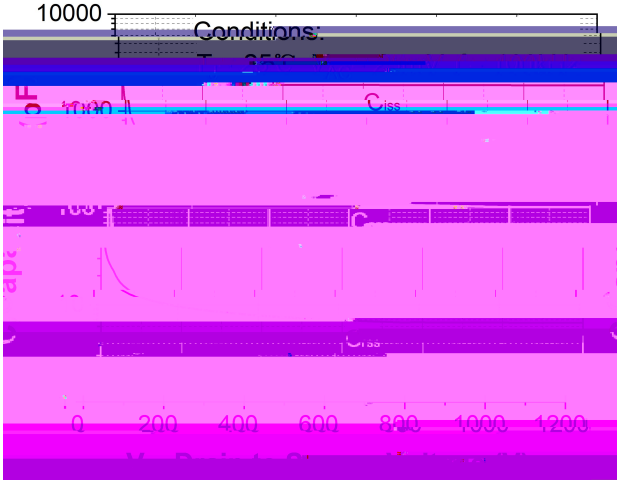










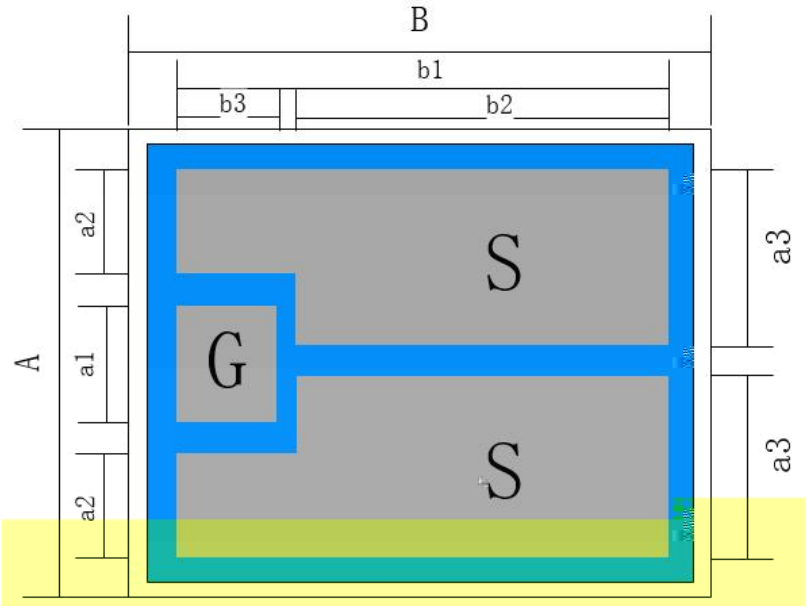


4 Mechanical parameters

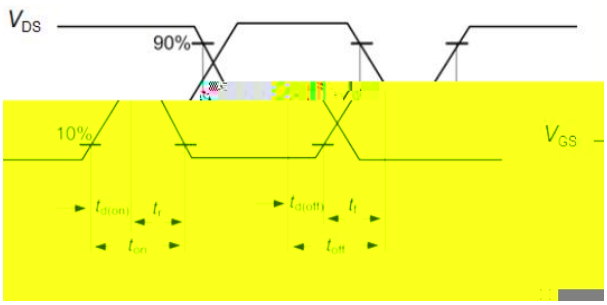
4.1 Dimensions and metallization

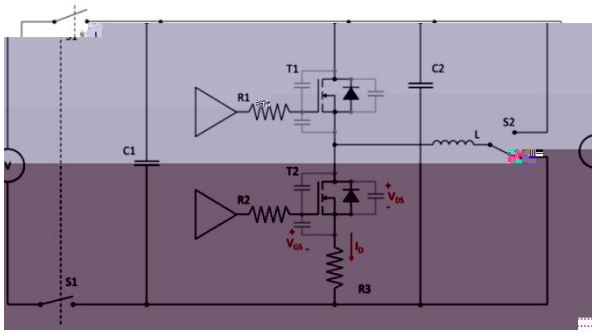
Parameter	Typical value	Unit	Metallization

4.2 Layout



5 Test conditions





SG2M035120BJ

1200V SiC Power MOSFET

Revision history

Document version	Date of release	Document stage	Description of changes
V01_00	2025-09-17	——	——
V01_01	2025-12-11	——	——
V01_02	2026-02-03	Final	——

Attention

RoHS compliance

REACH compliance

SG2M035120BJ